



High-Voltage Driver Applications

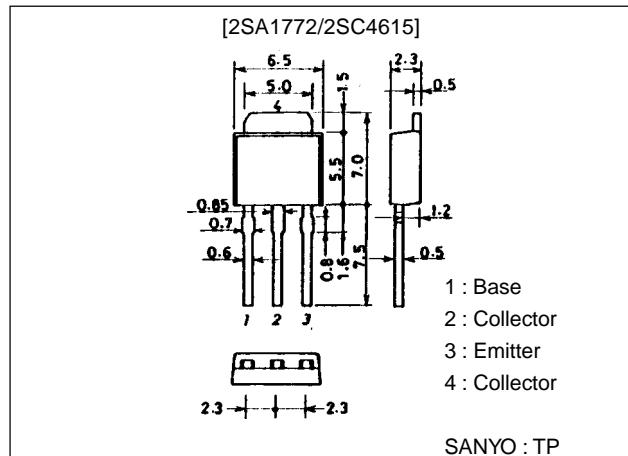
Features

- Large current capacity ($I_C=1A$).
- High breakdown voltage ($V_{CEO} \geq 400V$).

Package Dimensions

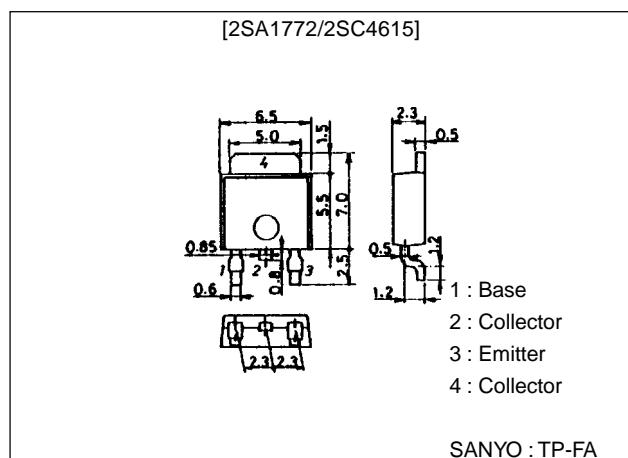
unit:mm

2045B



unit:mm

2044B



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SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

() : 2SA1772

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-400	V
Collector-to-Emitter Voltage	V_{CEO}		(-400	V
Emitter-to-Base Voltage	V_{EBO}		(-5	V
Collector Current	I_C		(-1	A
Collector Current (Pulse)	I_{CP}		(-2	A
Collector Dissipation	P_C		1	W
		$T_c=25^\circ\text{C}$	15	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

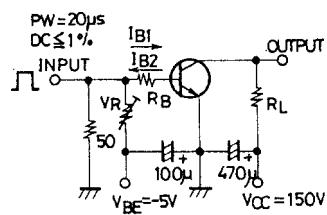
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)300\text{V}, I_E=0$			(-1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4\text{V}, I_C=0$			(-1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)10\text{V}, I_C=(-)100\text{mA}$	40*		200*	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)50\text{mA}$		(50)70		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)30\text{V}, f=1\text{MHz}$		(12)8		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C=(-)200\text{mA}, I_B=(-)20\text{mA}$			(-1.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(\text{sat})}$	$I_C=(-)200\text{mA}, I_B=(-)20\text{mA}$			(-1.0	V
Collector-to-Base Breakdown Voltage	$V_{(\text{BR})CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-400			V
Collector-to-Emitter Breakdown Voltage	$V_{(\text{BR})CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-400			V
Emitter-to-Base Breakdown Voltage	$V_{(\text{BR})EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-5			V
Turn-ON Time	t_{on}	See specified Test Circuit		(0.25)		μs
				0.11		μs
Storage Time	t_{stg}	See specified Test Circuit		(3.0)		μs
				4.0		μs
Fall Time	t_f	See specified Test Circuit		(0.3)		μs
				0.65		μs

* : The 2SA1772/2SC4615 are classified by 100mA h_{FE} as follows :

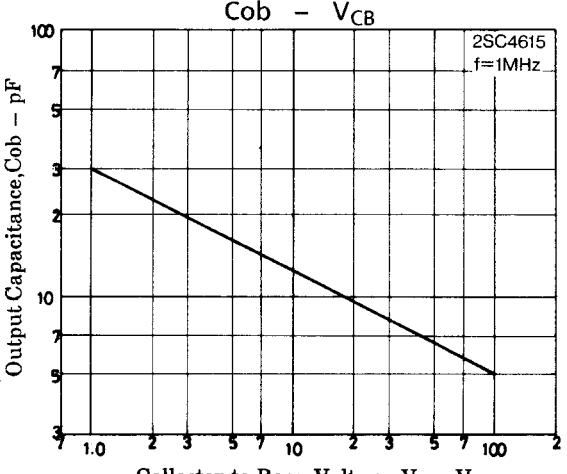
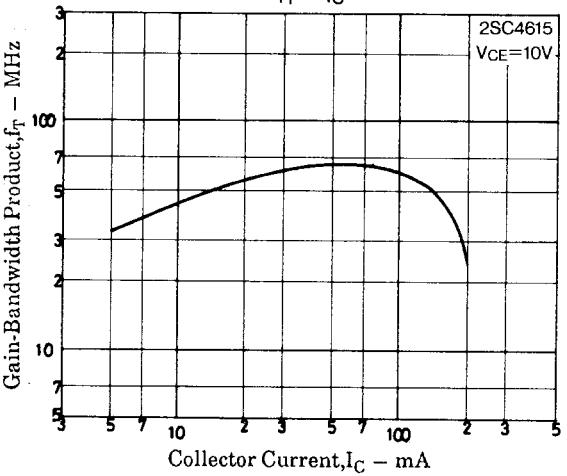
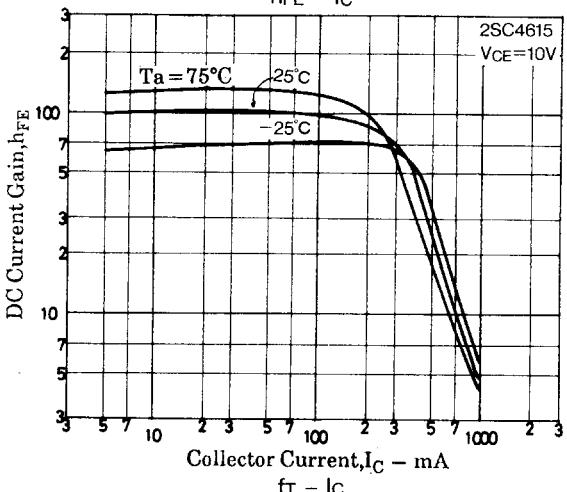
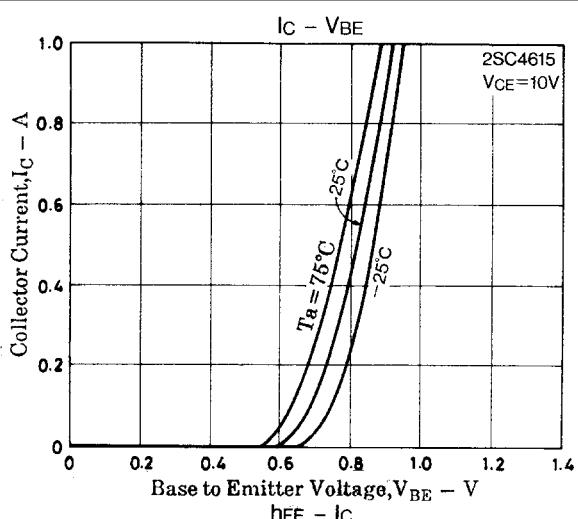
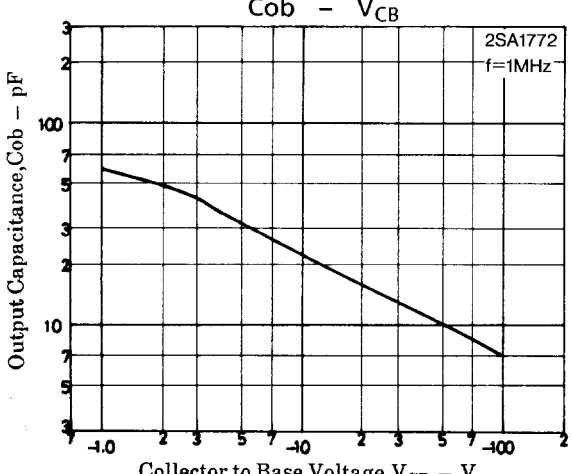
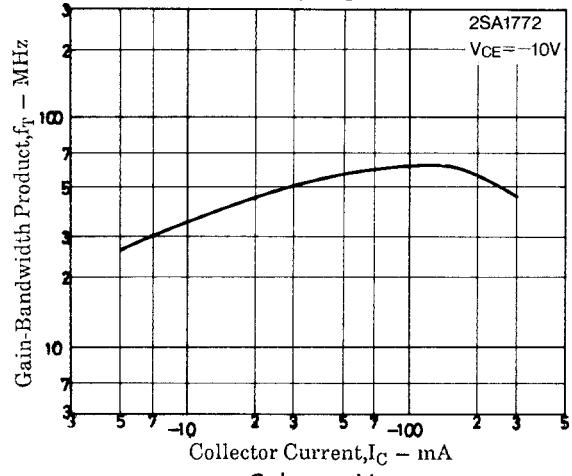
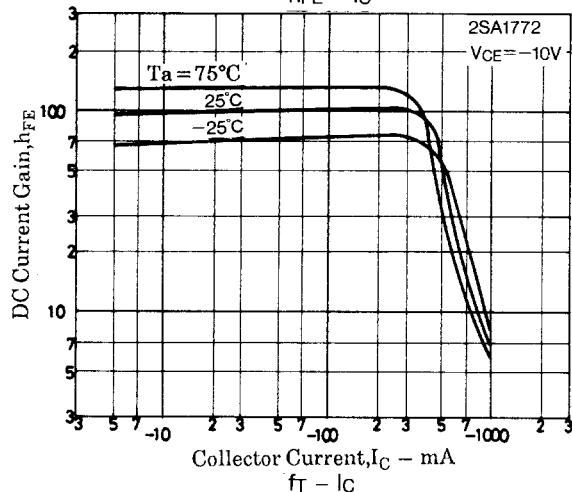
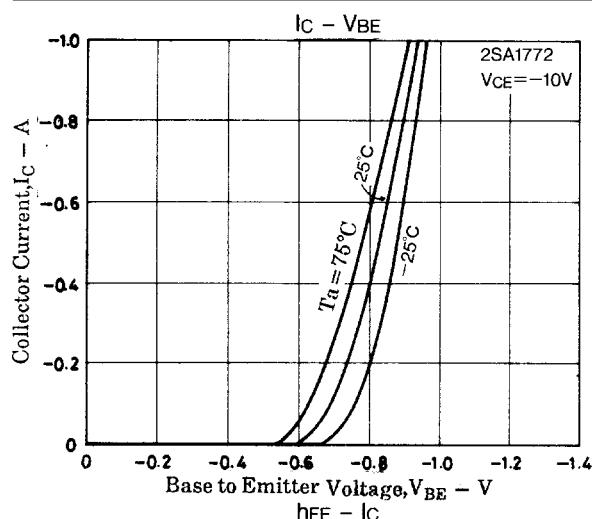
40	C	80	60	D	120	100	E	200
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Switching Time Test Circuit

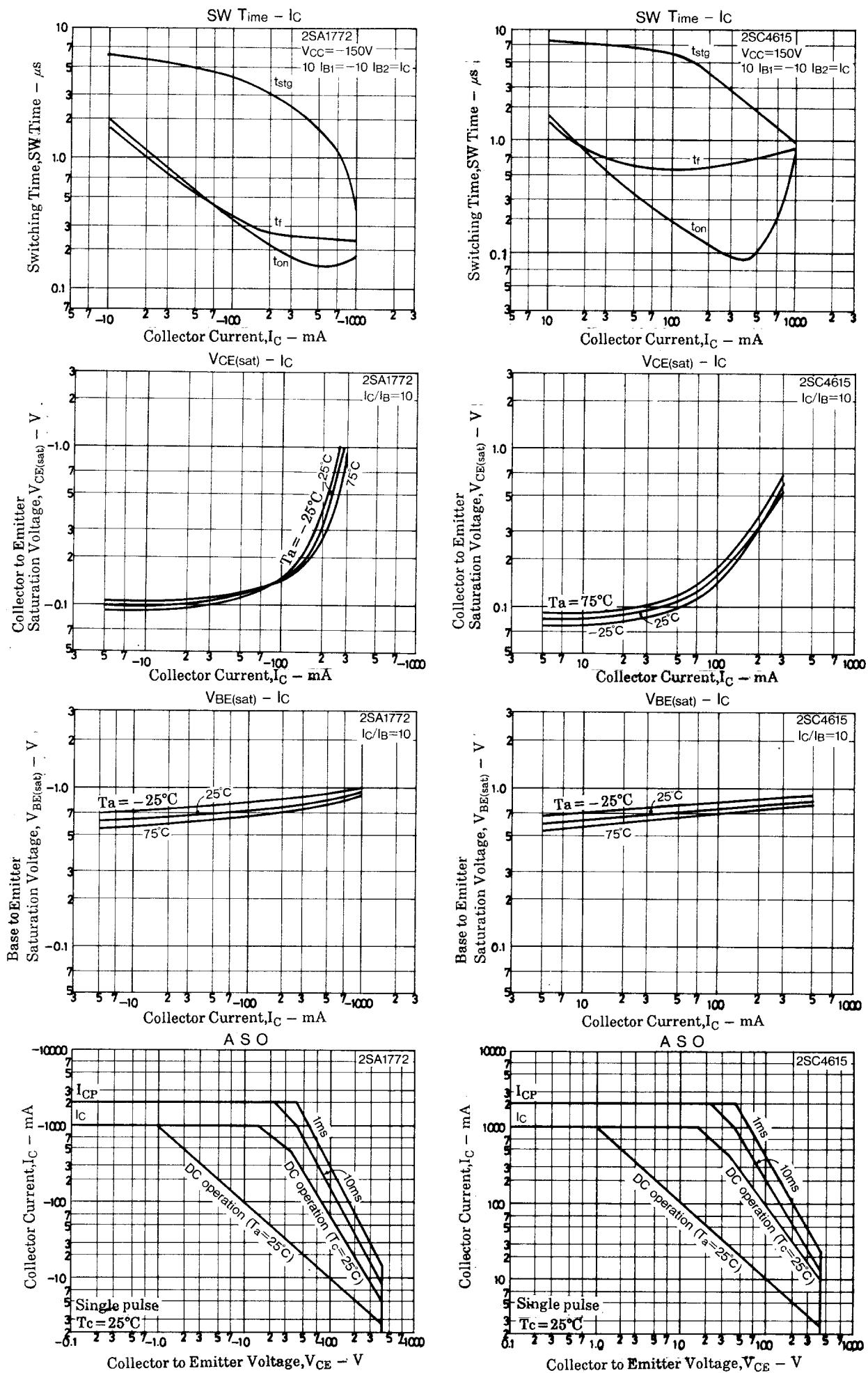


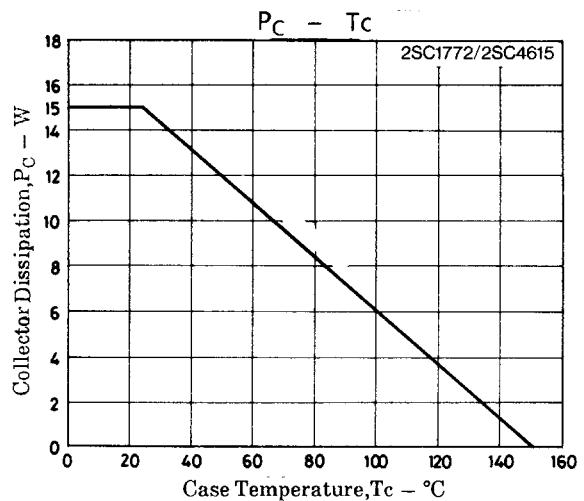
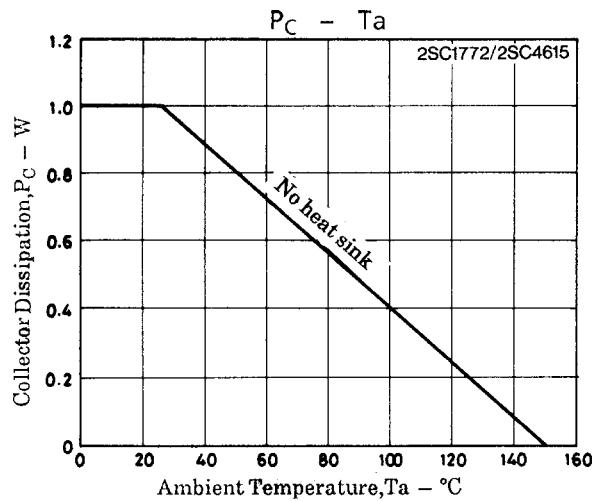
$PW=20\mu\text{s}$
 $DC \leq 1\%$
 $10I_{B1} = -10I_{B2} = I_C = 200\text{mA}$
 $R_L = 750\Omega, R_B = 50\Omega, \text{at } I_C = 200\text{mA}$
 (For PNP, the polarity is reversed.)
 Unit (resistance : Ω, capacitance : F)

2SA1772/2SC4615



2SA1772/2SC4615





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